



FORM PTO-1449  
(Equivalent)

U.S. Department of Commerce  
Patent and Trademark Office

U.S. Application Serial No.  
10/829,016

Atty. Docket No.  
AM-9230

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

Soo Young Choi et al.  
Applicants

(Use several sheets if necessary)

April 30, 2004  
Filing Date

Unknown  
Group

U. S. PATENT DOCUMENTS

Examiner Initial	Document Number	Issue Date	Name	Class	Subclass	Filing Date If Appropriate
<u>J.W.S.</u>	5,399,387	03/21/95	Law et al.	427	574	
<u>J.W.S.</u>	5,928,732	07/27/99	Law et al.	427	579	

U. S. PATENT APPLICATION DOCUMENTS

Examiner Initial	Document Number	Publication Date	Name	Class	Subclass	Filing Date
<u>J.W.S.</u>	2002/0146879	10/10/02	Fu et al.	438	230	12/21/01

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Publication Date	Name	Class	Subclass	Translation (If Appropriate)
<u>J.W.S.</u>	EP 1168427	01/02/02	Tan et al.	H01L	21/318	

Examiner

Date Considered

Stephen W. Smoot

December 31, 2005

Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Received: 6-23-04

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

S.W.S.

S. K. Kim et al., "A Novel Self-Aligned Coplanar Amorphous Silicon Thin Film Transistor", ISSN0098-0966X/98/2901 (1998).

S.W.S.

L. Kyung-ha, "A Study on Laser Annealed Polycrystalline Silicon Thin Film Transistors (TFTs) with SiNx Gate Insulator", Kyung Hee University, Ch. 2 & 4 (1998).

S.W.S.

Y. Park, "Bulk and interface properties of low-temperature silicon nitride films deposited by remote plasma enhanced chemical vapor deposition", Journal of Materials Science: Materials in Electronics, Vol. 12, pp. 515 - 522 (2001).

S.W.S.

A. Sazonov et al., "Low Temperature a-Si:H TFT on Plastic Films: Materials and Fabrication Aspects", Proc. 23<sup>rd</sup> International Conference on Microelectronics (MIEL 2002), Vol. 2, Niš, Yugoslavia (May 2002).

S.W.S.

D. B. Thomasson et al., "High Mobility Tri-Layer a-Si:H Thin Film Transistors with Ultra-Thin Active Layer", 1997 Society for Information Display International Symposium Digest of Technical Papers, Vol. 28, pp. 176 - 179 (May 1997).

Stephen N. Snoot  
Examiner

Date Considered

December 21, 2005

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AM-9230

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(Use several sheets if necessary)

Soo Young Choi et al.  
Applicants

April 20, 2004  
Filing Date

2813  
Group

U. S. PATENT DOCUMENTS

Examiner Initial	Document Number	Issue Date	Name	Class	Subclass	Filing Date If Appropriate
<u>S.W.J.</u>	6,040,022	03/21/00	Chang et al.	427	579	
<u>S.W.J.</u>	6,150,283	11/21/00	Ishiguro et al.	438	758	
<u>S.W.J.</u>	6,338,874	01/15/02 03/04/04	Law et al.	427	255.18	

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Examiner Initial	Document Number	Publication Date	Name	Class	Subclass	Filing Date
<u>S.W.J.</u>	2002/0006478A1	01/17/02	Yuda et al.	118	715	03/27/01
<u>S.W.J.</u>	2002/0189545A1	12/19/02	Matsumura et al.	219	390	05/14/02
<u>S.W.J.</u>	2003/0199175A1	10/23/03	Tang et al.	438	791	04/18/02
<u>S.W.J.</u>	2004/0043637A1	03/04/04	Aota et al.	438	791	08/29/03

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Examiner Date Considered

Stephen N. Smoot December 21, 2005

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Received: 10-13-05

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Yue Kuo, "Plasma Enhanced Chemical Vapor Deposited Silicon Nitride as a Gate Dielectric Film for Amorphous Silicon Thin Film Transistors – A Critical Review", *Vacuum*, vol. 51, no. 4, pages 741-745, Elsevier Science, Ltd., Pergamon Press, Great Britain, December 1998.

S.W.S.

International Search Report of corresponding PCT Application No. PCT/US2005/012832, mailed August 11, 2005

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